L	Hits	Search Text	DB	Time stamp
Number 45	4379783	hole recess trench gap cavity opening	TIGD? III	2004/01/16
45	43/9/83	noie recess trench gap cavity opening	USPAT; US-PGPUB;	2004/01/16 15:39
			EPO; JPO;	15:39
			DERWENT;	
			IBM TDB	
46	1803241	substrate wafer	USPAT;	2004/01/16
1.0	1000211	Substitute water	US-PGPUB;	15:39
			EPO; JPO;	13.33
			DERWENT;	
			IBM TDB	
47	1146415	electrode bump	USPAT;	2004/01/16
		_	US-PGPUB;	15:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
48	18550	interconnect\$3 adj2 (pattern film layer)	USPAT;	2004/01/16
			US-PGPUB;	15:40
	1		EPO; JPO;	
	1		DERWENT;	
49	4664	(holo rososs trongh san annity annity)	IBM_TDB	2004/01/16
30	4004	(hole recess trench gap cavity opening) and (substrate wafer) and (electrode	USPAT; US-PGPUB;	2004/01/16
		bump) and (interconnect\$3 adj2 (pattern	EPO; JPO;	15:44
		film layer))	DERWENT;	
			IBM TDB	
50	2174	257/668	USPAT;	2004/01/16
			US-PGPUB;	15:42
			EPO; JPO;	10112
			DERWENT;	
			IBM TDB	
51	2981	257/676	USPAT;	2004/01/16
			US-PGPUB;	15:42
			EPO; JPO;	
			DERWENT;	
52	740	257/600	IBM_TDB	
32	748	257/688	USPAT;	2004/01/16
		·	US-PGPUB;	15:42
			EPO; JPO; DERWENT;	
			IBM TDB	
53	340	257/694	USPAT;	2004/01/16
		···	US-PGPUB;	15:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
54	2165	257/698	USPAT;	2004/01/16
			US-PGPUB;	15:42
			EPO; JPO;	
			DERWENT;	
	^^^^	257/727	IBM_TDB	
55	2938	257/737	USPAT;	2004/01/16
			US-PGPUB;	15:43
			EPO; JPO;	
			DERWENT;	
56	2443	257/738	IBM_TDB USPAT;	2004/01/16
	2333	120., 700	US-PGPUB;	15:43
			EPO; JPO;	10.10
			DERWENT;	
			IBM TDB	
57	276	257/739	USPAT;	2004/01/16
			US-PGPUB;	15:43
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

Search History 1/16/04 3:44:15 PM

Page 1

58	3056	257/774	USPAT;	2004/01/16
			US-PGPUB;	15:43
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
59	3556	257/778	USPAT;	2004/01/16
			US-PGPUB;	15:43
			EPO; JPO;	1 20.13
			DERWENT;	
			IBM TDB	
60	957	257/782	USPAT;	2004/01/16
			US-PGPUB;	15:43
1			EPO; JPO;	13.13
1			DERWENT;	
			IBM TDB	
61	1482	257/783	USPAT;	2004/01/16
- -			US-PGPUB;	15:43
			EPO; JPO;	13.13
			DERWENT;	
			IBM TDB	
62	2329	257/784	USPAT;	2004/01/16
			US-PGPUB;	15:43
			EPO; JPO;	13.13
			DERWENT;	
			IBM TDB	
63	2372	257/786	USPAT;	2004/01/16
			US-PGPUB;	15:43
			EPO; JPO;	10.10
			DERWENT;	
			IBM TDB	
64	16528	257/668 257/676 257/688 257/694 257/698	USPAT;	2004/01/16
- •	1 3330	257/737 257/738 257/739 257/774 257/778	US-PGPUB;	15:43
		257/782 257/783 257/784 257/786	EPO; JPO;	10.10
			DERWENT;	
			IBM TDB	
65	488	((hole recess trench gap cavity opening)	USPAT;	2004/01/16
		and (substrate wafer) and (electrode	US-PGPUB;	15:44
		bump) and (interconnect\$3 adj2 (pattern	EPO; JPO;	
		film layer))) and (257/668 257/676	DERWENT;	
		257/688 257/694 257/698 257/737 257/738	IBM TDB	
		257/739 257/774 257/778 257/782 257/783		
		257/784 257/786)		